Abstracts

Long Term Stability of DROs Compared to Crystal Oscillators

K.R. Varian. "Long Term Stability of DROs Compared to Crystal Oscillators." 1987 MTT-S International Microwave Symposium Digest 87.2 (1987 Vol. II [MWSYM]): 583-586.

Guidelines are presented for GaAs FET DRO’s which when followed result in the DRO’s long term drift characteristics being similar to crystal oscillators. The guidelines fall into three categories: electrical stresses in the FET, fabrication issues of the DRO, and processing of the FET (a screening test for the GaAs FETs is described). Experimental data is included on a sample of units that support the proposed guidelines.

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